

Prof. Dr. EMİNE ÖZTÜRK

Kişisel Bilgiler

İş Telefonu: [+90 346 487 1976](tel:+903464871976) Dahili: 1976
E-posta: eozturk@cumhuriyet.edu.tr
Web: <https://avesis.cumhuriyet.edu.tr/eozturk>

Uluslararası Araştırmacı ID'leri

ORCID: 0000-0003-2508-0863
ScopusID: 7006384179
Yoksis Araştırmacı ID: 2697



Eğitim Bilgileri

Doktora, Sivas Cumhuriyet Üniversitesi, Fen Fakültesi, Fizik Bölümü, Türkiye 1995 - 2000
Yüksek Lisans, Sivas Cumhuriyet Üniversitesi, Fen Fakültesi, Fizik Bölümü, Türkiye 1992 - 1994
Lisans, Sivas Cumhuriyet Üniversitesi, Fen Fakültesi, Fizik Bölümü, Türkiye 1985 - 1989

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Kitap & Kitap Bölümleri

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